

**METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING**

APPARATUS

ABSTRACT

There is provided a technique that includes: (a) supplying a film-forming agent to the substrate having a recess on a surface thereof, the recess having a bottom surface formed by a first base and a side surface formed by a second base, and forming a first film on the first base with a thickness greater than a thickness of a first film formed on the second base; and (b) supplying an etching agent to the substrate, and removing the first film formed on the second base while leaving at least a part of the first film formed on the first base.

Fig. 1